

# 深圳市晶泰源电子有限公司

JTY D882

TRANSISTOR(NPN)

## FEATURES

Power dissipation

PCM:10W( $T_{amb}=25^{\circ}C$ )

Collector current

ICM:3.0A

Collector-base voltage

V(BR)CBO: 40V

Operating and storage junction temperature range

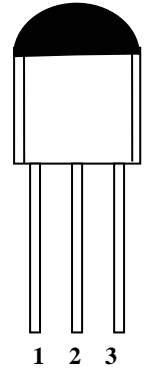
$T_J, T_{stg}: -65^{\circ}C$  to  $-150^{\circ}C$

T0-92

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS( $T_{amb}=25^{\circ}C$  unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=1mA, I_E=0$	40			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_C=1mA, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.5	$\mu A$
Collector cut-off current	$I_{Ceo}$	$V_{ce}=30V, I_B=0$			1.0	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6V, I_C=0$			0.1	$\mu A$
DC current gain	$H_{FE}$	$V_{ce}=5V, I_C=1mA$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=200mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2A, I_B=200mA$			2.0	V
Transition frequency	$f_T$	$V_{ce}=10V,$ $I_C=50mA$ $f=30MHZ$	50			MHZ

## CLASSIFICATION OF $h_{FE}(2)$

Rank	P	
Range	300-400	

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